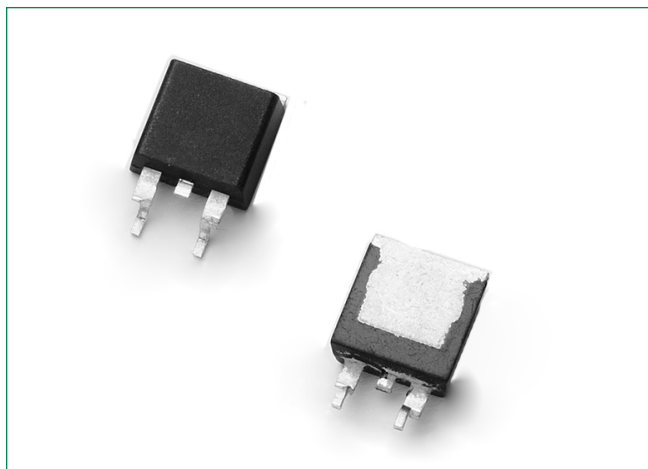


MAC4DHM

P6



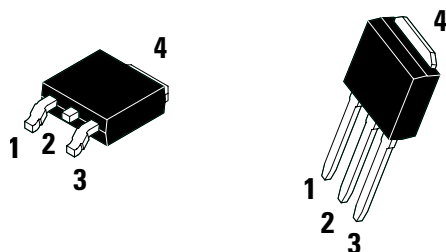
Description

The MAC4DHM is designed for high volume, low cost, industrial and consumer applications such as motor control; process control; temperature, light and speed control.

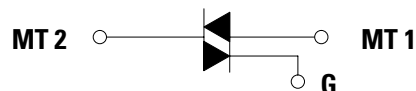
Features

- Small Size Surface Mount DPAK Package
- Passivated Die for Reliability and Uniformity
- Four-Quadrant Triggering
- Blocking Voltage to 600 V
- On-State Current Rating of 4.0 A RMS at 93°C
- Low Level Triggering and Holding Characteristics
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B > 8000 V
Machine Model, C > 400V
- Lead-Free Packages are Available

Pin Out



Functional Diagram



Maximum Ratings ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_J = -40^\circ$ to 110°C)	V_{DRM}' V_{RRM}	600	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_C = 93^\circ\text{C}$)	I_T (RMS)	4.0	A
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_C = 110^\circ\text{C}$)	I_{TSM}	40	A
Circuit Fusing Consideration ($t = 8.3$ msec)	I^2t	6.6	A ² sec
Peak Gate Current (Pulse Width ≤ 20 μsec , $T_C = 108^\circ\text{C}$)	I_{GM}	4.0	A
Peak Gate Power (Pulse Width ≤ 10 μsec , $T_C = 108^\circ\text{C}$)	P_{GM}	2.0	W
Peak Gate Voltage (Pulse Width ≤ 20 μsec , $T_C = 93^\circ\text{C}$)	V_{GM}	5.0	V
Average Gate Power ($t = 8.3$ msec, $T_C = 108^\circ\text{C}$)	$P_{\text{G(AV)}}$	1.0	W
Operating Junction Temperature Range	T_J	-40 to +110	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (AC) Junction-to-Ambient Junction-to-Ambient (Note 2)	$R_{\theta\text{JC}}$ $R_{\theta\text{JA}}$ $R_{\theta\text{JA}}$	3.5 88 80	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	$^\circ\text{C}$

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.
 3. 1/8" from case for 10 seconds.

Electrical Characteristics - OFF ($T_J = 25^\circ\text{C}$ unless otherwise noted ; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Repetitive Blocking Current ($V_D = V_{\text{DRM}} = V_{\text{RRM}}$, Gate Open)	I_{DRM}' I_{RRM}	-	-	0.01 2.0	mA

Electrical Characteristics - ON ($T_J = 25^\circ\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak On-State Voltage (Note 4) ($I_{\text{TM}} = \pm 6.0$ A)	V_{TM}	-	1.3	1.6	V
Gate Trigger Current (Continuous dc) ($V_D = 12$ V, $R_L = 100$ Ω)	I_{GT}	-	1.8 2.1 2.4 4.2	5.0 5.0 5.0 10	mA
Holding Current ($V_D = 12$ V, Gate Open, Initiating Current = ± 200 mA)	I_H	-	1.5	15	mA
Gate Non-Trigger Voltage (Continuous dc) – ($V_D = 12$ V, $R_L = 100$ Ω , $T_J = 110^\circ\text{C}$) All Four Quadrants	V_{GD}	0.1	0.4	-	V
Latching Current	I_L	-	1.75 5.2 2.1 2.2	10 10 10 10	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12$ V, $R_L = 100$ Ω)	V_{GT}	0.5 0.5 0.5 0.5	0.62 0.57 0.65 0.74	1.3 1.3 1.3 1.3	V

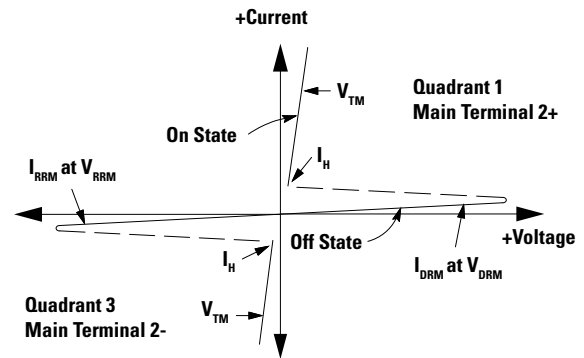
4. Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle $\leq 2\%$.

Dynamic Characteristics

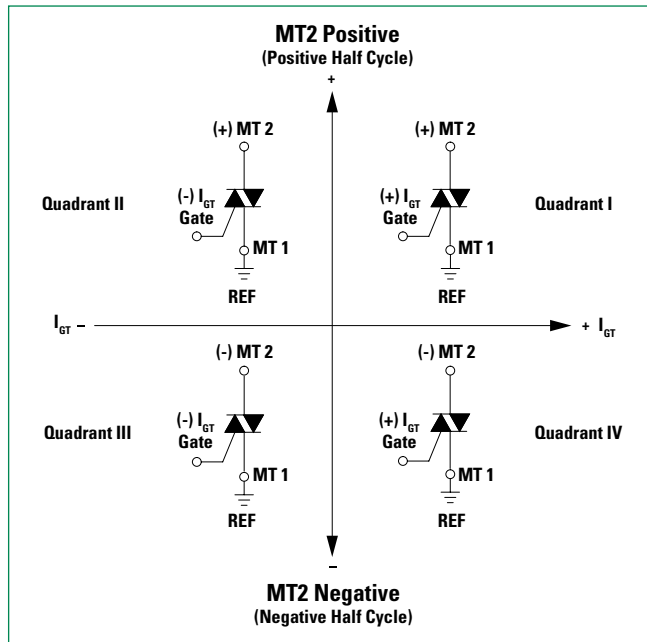
Characteristic	Symbol	Min	Typ	Max	Unit
Rate of Change of Commutating Current ($V_D = 200\text{ V}$, $I_{TM} = 1.8\text{ A}$, Commutating $dv/dt = 1.0\text{ V}/\mu\text{sec}$, $T_J = 110^\circ\text{C}$, $f = 250\text{ Hz}$, $CL = 5.0\text{ }\mu\text{fd}$, $LL = 80\text{ mH}$, $RS = 56\text{ }\Omega$, $CS = 0.03\text{ }\mu\text{fd}$) With snubber see Figure 11	$(di/dt)_c$	-	3.0	-	A/ms
Critical Rate of Rise of Off-State Voltage ($V_D = 0.67 \times V_{DRM}$, Exponential Waveform, Gate Open, $T_J = 110^\circ\text{C}$)	dV/dt	20	-	-	V/ μs

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All Polarities are referenced to MT1.
With in-phase signals (using standard AC lines) quadrants I and III are used

Figure 1. Typical RMS Current Derating

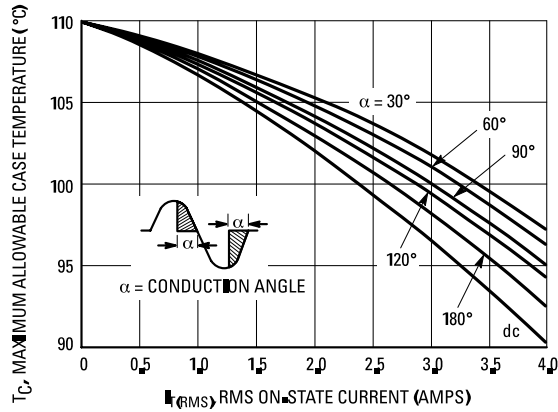


Figure 2. On-State Power Dissipation

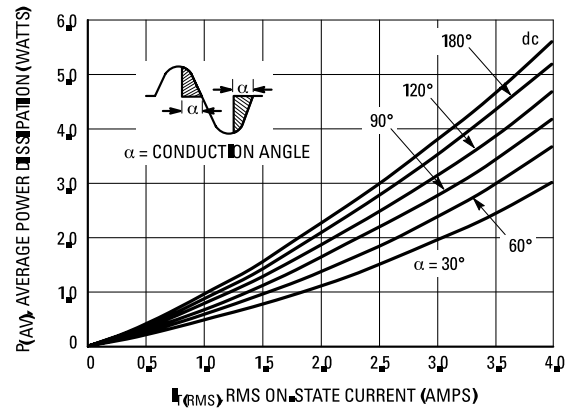


Figure 3. On-State Characteristics

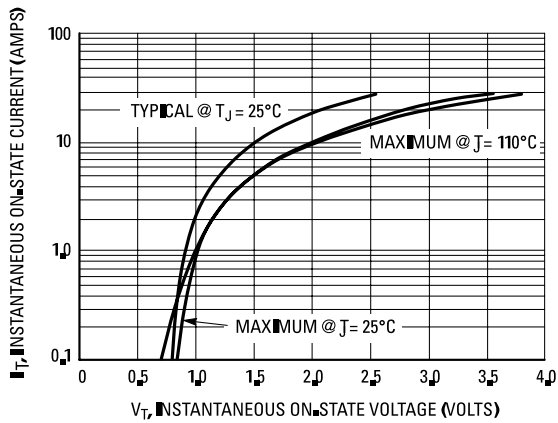


Figure 4. Transient Thermal Response

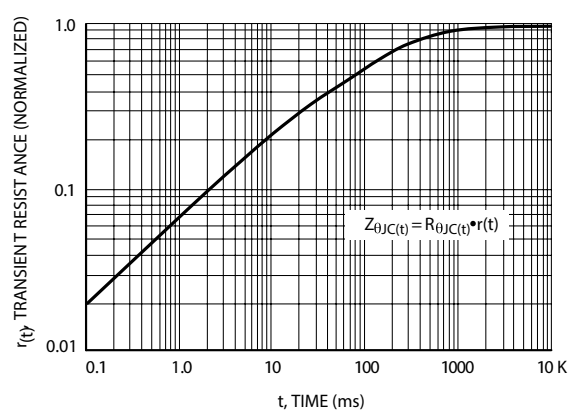


Figure 5. Typical Gate Trigger Current vs. Junction Temperature

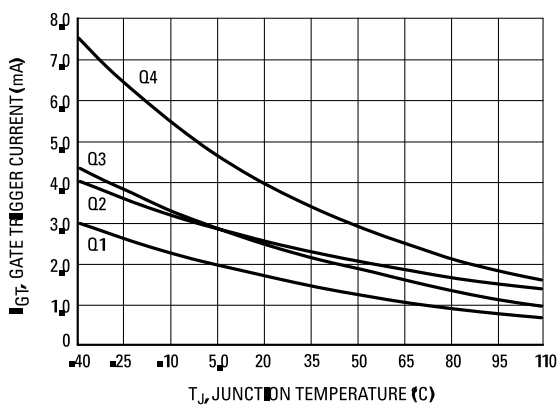
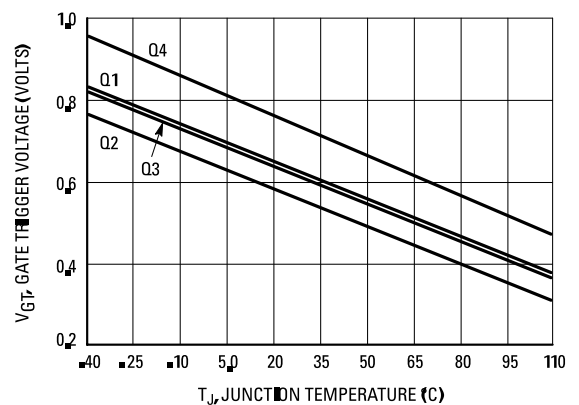


Figure 6. Typical Gate Trigger Voltage vs. Junction Temperature



A line graph showing the relationship between Holding Current (I_H) in mA and Junction Temperature (T) in $^{\circ}\text{C}$. The y-axis ranges from 0 to 5.0 mA with major grid lines every 1.0 mA. The x-axis ranges from -40 to 110 $^{\circ}\text{C}$ with major grid lines every 15 $^{\circ}\text{C}$. Two curves are plotted: 'MT2 NEGATIVE' and 'MT2 POSITIVE'. Both curves show a decreasing trend as temperature increases. The 'MT2 NEGATIVE' curve starts at approximately 3.6 mA at -40 $^{\circ}\text{C}$ and ends at approximately 0.6 mA at 110 $^{\circ}\text{C}$. The 'MT2 POSITIVE' curve starts at approximately 2.6 mA at -40 $^{\circ}\text{C}$ and ends at approximately 0.4 mA at 110 $^{\circ}\text{C}$.

T, JUNCTION TEMPERATURE ($^{\circ}\text{C}$)	MT2 NEGATIVE (I_H in mA)	MT2 POSITIVE (I_H in mA)
-40	3.6	2.6
-25	3.0	2.2
-10	2.5	1.8
5	2.1	1.5
20	1.8	1.2
35	1.5	1.0
50	1.3	0.8
65	1.1	0.7
80	0.9	0.6
95	0.7	0.5
110	0.6	0.4

The graph shows the latching current I_L in mA on the y-axis (0 to 12) versus the junction temperature T_J in °C on the x-axis (-40 to 110). Four curves are plotted, labeled Q1, Q2, Q3, and Q4. Curve Q2 is the highest, starting at approximately 10.5 mA at -40°C and decreasing to about 1.5 mA at 110°C. Curve Q4 starts at approximately 3.5 mA at -40°C and decreases to about 1.0 mA at 110°C. Curve Q1 starts at approximately 3.0 mA at -40°C and decreases to about 0.8 mA at 110°C. Curve Q3 is the lowest, starting at approximately 2.5 mA at -40°C and decreasing to about 0.5 mA at 110°C. All curves show a decreasing trend as temperature increases.

The graph shows the static dv/dt capability of the MAC4DHM MOSFET as a function of gate-MT1 resistance. The y-axis represents $STATIC\ dv/dt\ (V/\mu s)$ on a linear scale from 5 to 40. The x-axis represents $GATE-MT1\ RESISTANCE\ (\Omega)$ on a logarithmic scale from 100 to 10K. The curve starts at approximately 27 $V/\mu s$ for 100 Ω , remains relatively flat until about 500 Ω , then drops sharply to about 21 $V/\mu s$ at 10K Ω . Operating conditions are noted as $V_D = 400V$ and $T_J = 110^\circ C$.

GATE-MT1 RESISTANCE (Ω)	STATIC dv/dt ($V/\mu s$)
100	~27
500	~26
1000	~23
10000	~21

$\frac{dv}{dt}(c)$, RATE OF RISE OF COMMUTATING VOLTAGE (V/ μ s)

$V_{PK} = 400 \text{ V}$

$T_J = 110^\circ\text{C}$ 100°C 90°C

$f = \frac{1}{2 t_{sw}}$

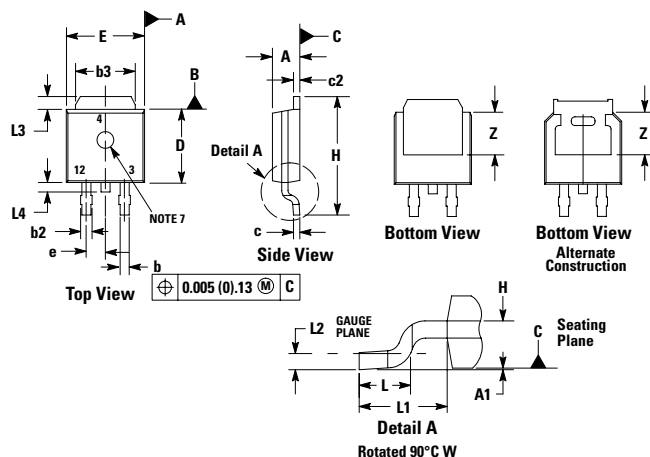
V_{DSM}

$\frac{di}{dt} = \frac{6fM}{1000}$

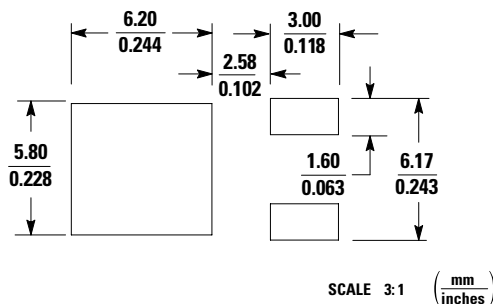
$\frac{di}{dt}(c)$, RATE OF CHANGE OF COMMUTATING CURRENT (A/ms)

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Specifications are subject to change without notice.
Revised: 09/01/20

Dimensions



Soldering Footprint

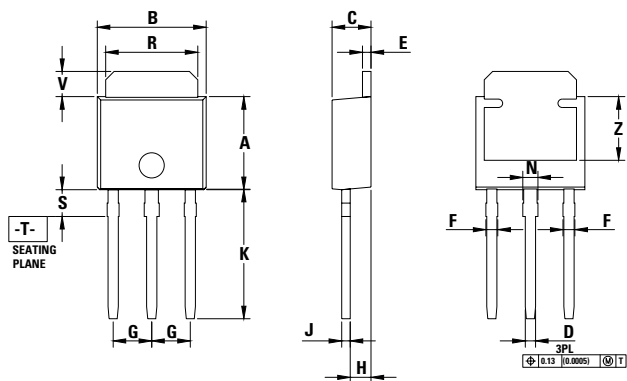


Dim	Inches		Millimeters	
	Min	Max	Min	Max
A	0.087	0.094	2.20	2.40
A1	0.000	0.005	0.00	0.12
b	0.022	0.030	0.55	0.75
b2	0.026	0.033	0.65	0.85
b3	0.209	0.217	5.30	5.50
c	0.019	0.023	0.49	0.59
c2	0.019	0.023	0.49	0.59
D	0.213	0.224	5.40	5.70
E	0.252	0.260	6.40	6.60
e	0.091		2.30	
H	0.374	0.406	9.50	10.30
L	0.058	0.070	1.47	1.78
L1	0.114		2.90	
L2	0.019	0.023	0.49	0.59
L3	0.053	0.065	1.35	1.65
L4	0.028	0.039	0.70	1.00
Z	0.154	-	3.90	-

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982.
2. CONTROLLING DIMENSION: INCH. STYLE 6: PIN 1. MT1
3. MT2
4. GATE
5. MT2

Dimensions

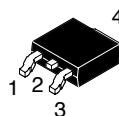
DDAK-3
Case 369D-01
Issue B
T0251-3L POD



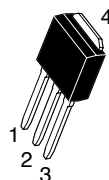
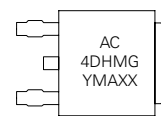
Dim	Inches		Millimeters	
	Min	Max	Min	Max
A	0.213	0.224	5.40	5.70
B	0.252	0.260	6.40	6.60
C	0.087	0.094	2.20	2.40
D	0.024	0.030	0.60	0.75
E	0.022	0.026	0.55	0.65
F	0.023	0.031	0.58	0.78
G	0.091 TYP.		2.30 TYP.	
H	0.046	0.050	1.18	1.28
J	0.019	0.023	0.49	0.59
K	0.291	0.315	7.40	8.00
N	0.031	0.039	0.78	0.98
R	0.209	0.217	5.30	5.50
S	0.063 TYP.		1.60 TYP.	
V	0.053	0.065	1.35	1.65
Z	0.150 TYP.		3.80 TYP.	

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH. STYLE 6: PIN 1: MT1
3. MT2
4. GATE
5. MT2

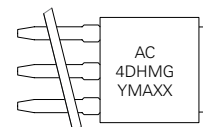
Part Marking System



DDAK-3
Case 369C
Style 6



DDAK-3
Case 369D
Style 6



AC4DCx = Device Code
x = D, M, or N
Y = Year
M = Month
A = Assembly Site
XX = Lot Serial Code
G = Pb-Free Package

Pin Assignment	
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

Ordering Information

Device	Package Type	Package	Shipping
MAC4DHM-001	DDAK-3	369D	4000 Units / Box
MAC4DHM-001G	DDAK-3 (Pb-Free)	369D	4000 Units / Box
MAC4DHMT4	DDAK-3	369C	2500 / Tape & Reel
MAC4DHMT4G	DDAK-3 (Pb-Free)	369C	2500 / Tape & Reel